ERRATA

Erratum: Dominant density parameters and local pseudopotentials for simple metals [Phys. Rev. B 51, 14 001 (1995)]

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[S0163-1829(96)07319-5]

Although the underlying all-electron calculations employed the correct local density approximation for exchange and correlation, the pseudopotential calculations for solids inadvertently used the local field correction for exchange alone. The corrected universal (U) and individual (I) pseudopotential parameters are given here.

	U		I	
Metal	α	R	α	R
Be	4.547	0.197	4.557	0.192
Al	3.633	0.334	3.572	0.317
Ga	3.539	0.365	3.278	0.318
Sn	3.367	0.444	3.084	0.386
Pb	3.334	0.466	2.950	0.403
In	3.397	0.423	3.150	0.387
Tl	3.360	0.439	2.948	0.400
Mg	3.493	0.383	3.505	0.383
Li	3.546	0.361	4.113	0.342
Ca	3.186	0.536	3.264	0.540
Sr	3.088	0.611	3.176	0.614
Ba	3.000	0.648	3.113	0.651
Na	3.074	0.528	3.499	0.494
K	2.806	0.745	3.321	0.683
Rb	2.749	0.823	3.197	0.760
Cs	2.692	0.919	3.138	0.848

These parameters and the resulting calculated properties differ at most by a few percent from those of the published article—not enough to change any of its qualitative conclusions. A corrected copy of the article is available from the authors, or from the Physics Auxiliary Publication Service (PAPS) of the American Institute of Physics.[1]

[1] See AIP document no. PAPS PRBMB-53-13193-36 for 36 pages of the complete corrected manuscript. Order by PAPS number and journal reference from American Institute of Physics, Physics Auxiliary Publication Service, Carolyn Gehlbach, 500 Sunnyside Boulevard, Woodbury, New York 11797-2999. Fax: 516-576-2223, e-mail: paps@aip.org. The price is $1.50 for each microfiche (98 pages) or $5.00 for photocopies of up to 30 pages, and $0.15 for each additional page over 30 pages. Airmail additional. Make checks payable to the American Institute of Physics in U.S. dollars drawn on a U.S. bank.

Erratum: In-plane dispersion relations of InAs/AlSb/GaSb/AlSb/InAs interband resonant-tunneling diodes [Phys. Rev. B 52, 14 025 (1995)]

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The second and last basis function should read

$$|2\rangle=|\tfrac{3}{2},\tfrac{1}{2}\rangle=-\sqrt{\tfrac{2}{3}}|Z\uparrow\rangle+\sqrt{\tfrac{1}{6}}|(X+iY)\downarrow\rangle \quad \text{and} \quad |8\rangle=|\tfrac{1}{2},-\tfrac{1}{2}\rangle=\sqrt{\tfrac{1}{3}}|Z\downarrow\rangle-\sqrt{\tfrac{1}{3}}|(X-iY)\uparrow\rangle.$$

$-\frac{3}{2}F_4^+$ should be changed to $-\sqrt{\frac{3}{2}}F_4^+$ in matrix *HA* and $\sqrt{\frac{3}{2}}Pk^+$ should be changed to $\sqrt{\frac{2}{3}}Pk^+$ in matrix *HC*.

The authors would like to thank P. Gassot for pointing out these differences between the original manuscript and the printed version.

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Erratum: Coarsening and slope evolution during unstable epitaxial growth [Phys. Rev. B 52, 14 263 (1995)]

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The received date for this manuscript was inadvertently misprinted. It should read as follows: (Received 7 June 1995).

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